TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCA8026

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 1.8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}|$ =100 S (typ.)
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

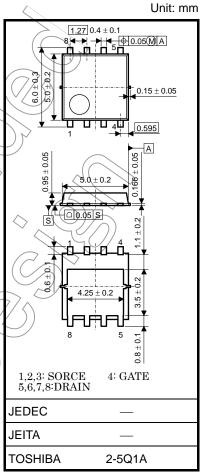
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	30	V
Gate-source voltage		V _{GSS}	±20	/ (v
Drain current	DC (Note 1)	ID	45	A
	Pulsed (Note 1)	IDP	135	^
Drain power dissipation	on $(Tc = 25^{\circ}C)$	(PD \	45 <	\ w
Drain power dissipation (t = 10 s) (Note 2a)		PP	2.8	N N
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	(1.6)	W
Single-pulse avalanche energy (Note 3)		EAS	263	mJ
Avalanche current		I _{AR}	45	Α
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	3.4	mJ
Channel temperature		Tch	150	°C
Storage temperature range		T _{stg}	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Ha

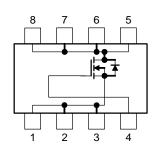
reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

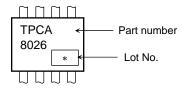
Circuit Configuration



Thermal Characteristics

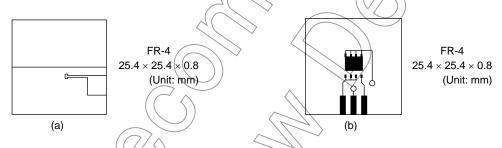
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case $(\mbox{Tc} = 25\mbox{°C}) \label{eq:Tc}$	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	°C/W

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{Ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, AR = 45 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture
(01) for the first week of the year, continuing up to 52 or 53)

Year of manufacture (The last digit of the year)

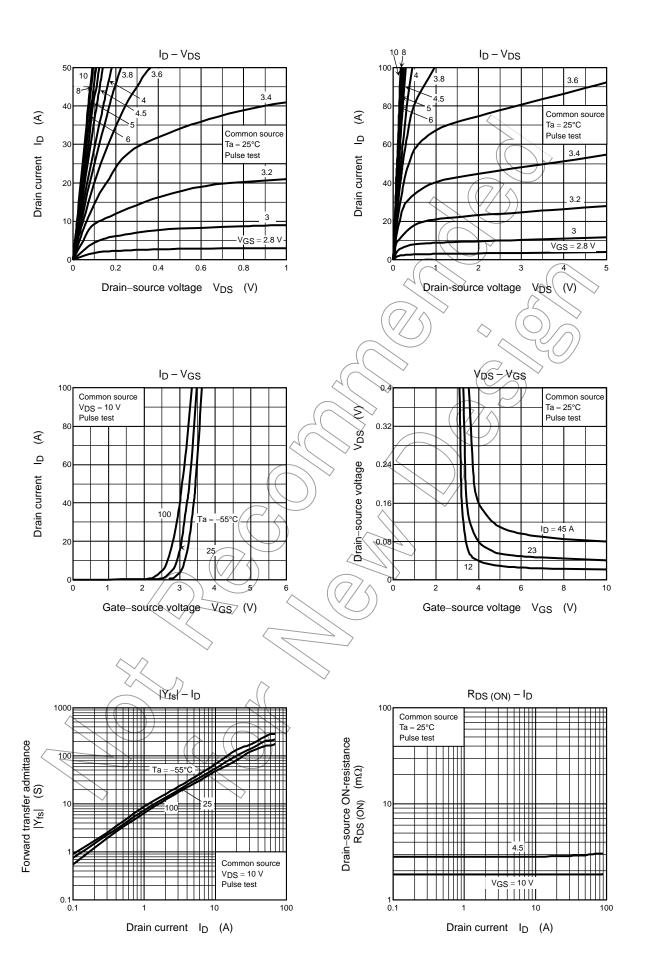
Electrical Characteristics (Ta = 25°C)

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	10	_	_		
Gate threshold vo	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	1.3) >_	2.5	V	
Drain-source ON-resistance		Б	V _{GS} = 4.5 V, I _D = 23 A	<u> </u>	2.7	4.5	- mΩ	
		R _{DS} (ON)	V _{GS} = 10 V, I _D = 23 A)	1.8	2.2		
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 23 A	50	100	_	S	
Input capacitance		C _{iss}		² —	4200	_		
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	1000	_	pF	
Output capacitance		C _{oss}			1400	7		
Switching time	Rise time	t _r	VGS 10 V	-(15	> _	ns	
	Turn-on time	t _{on}		VGS OV	30	_		
	Fall time	t _f			36	_		
	Turn-off time	t _{off}	$V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$, $t_W = 10 \mu \text{s}$) —	111	_		
Total gate charge (gate-source plus		Qg		_	113			
Gate-source charge 1		Q _{gs1}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$	_	13	_	nC	
Gate-drain ("miller") charge		Qgd		_	42	_		

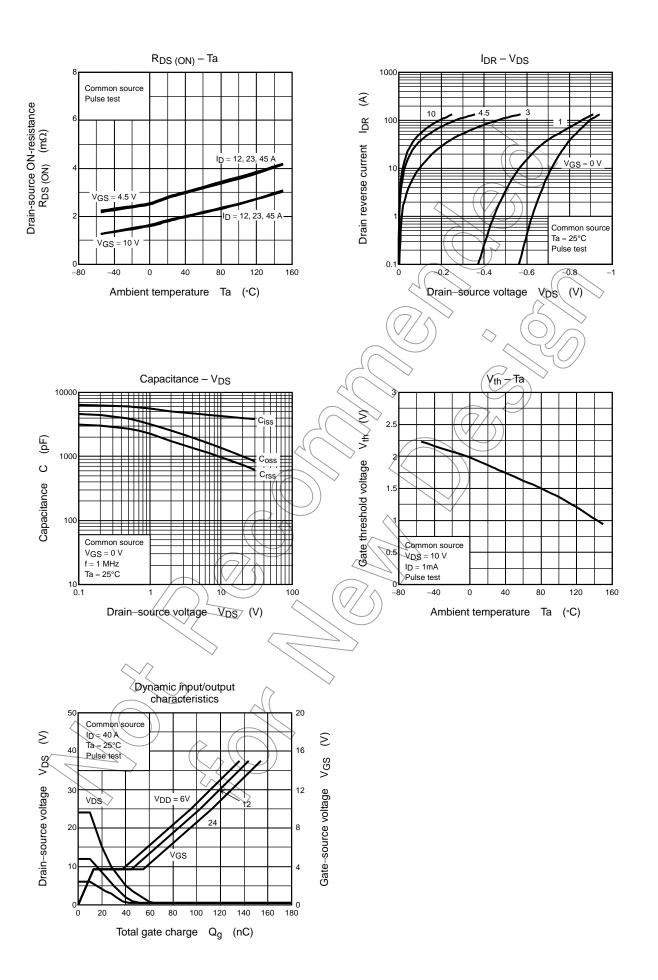
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note-1)	I _{DRP}	_	_	_	135	Α
Forward voltage (diode)	VDSF	I _{DR} = 45 A, V _{GS} = 0 V	_	_	-1.2	V

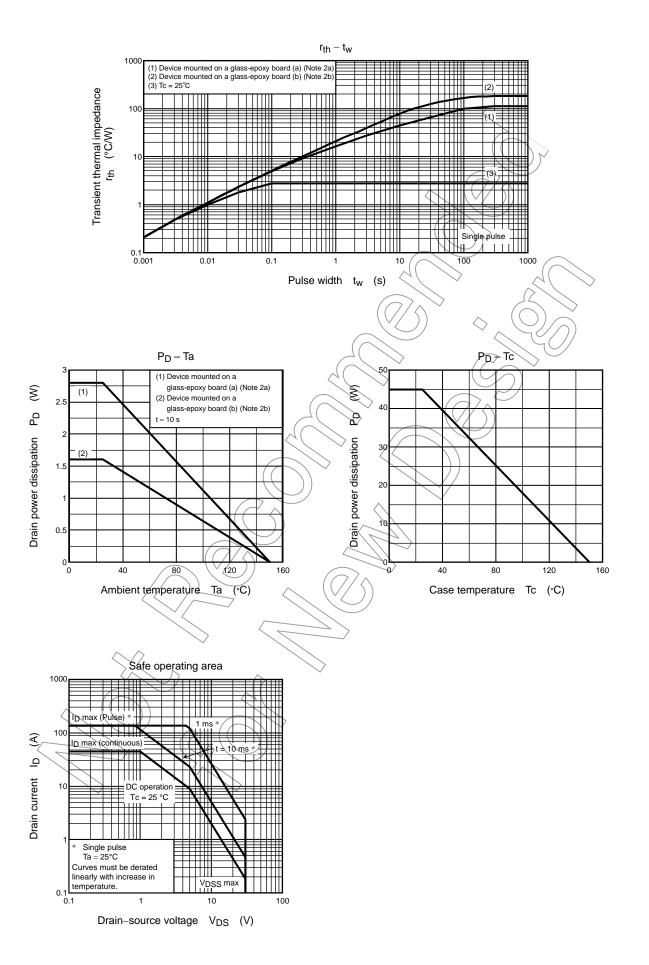




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